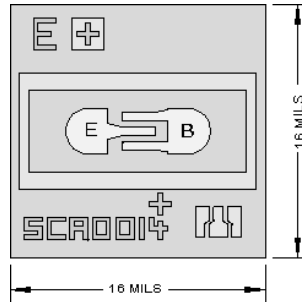


**Chip Type 2C4261**  
**Geometry 0014**  
**Polarity PNP**

**Generic Packaged Parts:**  
**2N4260, 2N4261**



[Request Quotation](#)

Chip type **2C4261** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:**

Designed for low voltage, low gain RF amplifier applications.

**Part Numbers:**

[2N4261](#), 2N4261UB, 2N4260, 2N4260UB, SD4261, SD4261F, SQ4261, SQ4261F

**Features: Special Characteristics**

$f_t = 1.8 \text{ GHz (typ) at } 10 \text{ mA/10V}$

| Mechanical Specifications |                   |                     |
|---------------------------|-------------------|---------------------|
| Metallization             | Top               | Al - 12 kÅ min.     |
|                           | Backside          | Au - 6.5 kÅ nom.    |
| Bonding Pad Size          | Emitter           | 2.1 mils x 2.1 mils |
|                           | Base              | 2.1 mils x 2.1 mils |
| Die Thickness             | 8 mils nominal    |                     |
| Chip Area                 | 16 mils x 16 mils |                     |
| Top Surface               | Silox Passivated  |                     |

| Electrical Characteristics |                                                     |     |     |      |
|----------------------------|-----------------------------------------------------|-----|-----|------|
| $T_A = 25^\circ\text{C}$   |                                                     |     |     |      |
| Parameter                  | Test conditions                                     | Min | Max | Unit |
| $BV_{CEO}$                 | $I_C = 10.0 \text{ mA}, I_B = 0$                    | 15  | --- | V dc |
| $BV_{CBO}$                 | $I_C = 10 \mu\text{A}, I_E = 0$                     | 15  | --- | V dc |
| $BV_{EBO}$                 | $I_E = 10 \mu\text{A}, I_C = 0$                     | 4.5 | --- | V dc |
| $h_{FE}$                   | $I_C = 10 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$ | 30  | 150 | ---  |

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*